

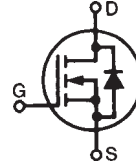
# HiPerFET™ Power MOSFETs Q-Class

N-Channel Enhancement Mode  
Avalanche Rated, High dv/dt, Low Q<sub>g</sub>  
Low intrinsic R<sub>g</sub>, low t<sub>rr</sub>

IXFK 30N100Q2  
IXFX 30N100Q2

V<sub>DSS</sub> = 1000 V  
I<sub>D25</sub> = 30 A  
R<sub>DS(on)</sub> = 0.40 Ω

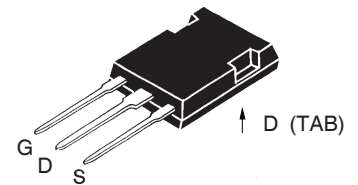
t<sub>rr</sub> ≤ 300 ns



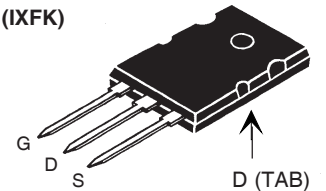
## Preliminary Data Sheet

Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	1000	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C; R <sub>GS</sub> = 1 MΩ	1000	V
V <sub>GS</sub>	Continuous	±30	V
V <sub>GSM</sub>	Transient	±40	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	30	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	120	A
I <sub>AR</sub>	T <sub>C</sub> = 25°C	30	A
E <sub>AR</sub>	T <sub>C</sub> = 25°C	60	mJ
E <sub>AS</sub>	T <sub>C</sub> = 25°C	4.0	J
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , di/dt ≤ 100 A/μs, V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C, R <sub>G</sub> = 2 Ω	20	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	735	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6 mm (0.063 in) from case for 10 s	300	°C
M <sub>d</sub>	Mounting torque	TO-264	0.9/6 Nm/lb.in.
Weight		PLUS-247	6 g
		TO-264	10 g

## PLUS247™ (IXFX)



## TO-264 AA (IXFK)



G = Gate  
S = Source

D = Drain  
TAB = Drain

Symbol	Test Conditions	Characteristic Values (T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 3mA	1000		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 8 mA	2.5		5.0 V
I <sub>GSS</sub>	V <sub>GS</sub> = ±30 V <sub>DC</sub> , V <sub>DS</sub> = 0			±200 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0 V			50 μA 2 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			0.40 Ω

## Features

- Double metal process for low gate resistance
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Avalanche energy and current rated
- Fast intrinsic Rectifier

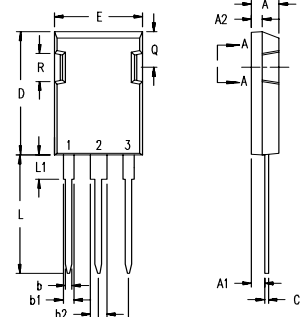
## Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
<b>g<sub>fs</sub></b>	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 0.5 • I <sub>D25</sub> , pulse test	20	30	S
<b>C<sub>iss</sub></b>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		8200	pF
<b>C<sub>oss</sub></b>			760	pF
<b>C<sub>rss</sub></b>			140	pF
<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub> R <sub>G</sub> = 1.0 Ω (External),		22	ns
<b>t<sub>r</sub></b>			14	ns
<b>t<sub>d(off)</sub></b>			60	ns
<b>t<sub>f</sub></b>			10	ns
<b>Q<sub>g(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub>		186	nC
<b>Q<sub>gs</sub></b>			46	nC
<b>Q<sub>gd</sub></b>			82	nC
<b>R<sub>thJC</sub></b>	TO-264			0.17 K/W
<b>R<sub>thCK</sub></b>			0.15	K/W

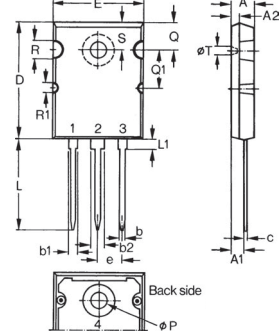
**Source-Drain Diode**

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
<b>I<sub>S</sub></b>	V <sub>GS</sub> = 0 V			30 A
<b>I<sub>SM</sub></b>	Repetitive; pulse width limited by T <sub>JM</sub>			120 A
<b>V<sub>SD</sub></b>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
<b>t<sub>rr</sub></b>	I <sub>F</sub> = 25A, -di/dt = 100 A/μs, V <sub>R</sub> = 100 V		1	250 ns
<b>Q<sub>RM</sub></b>			10	μC
<b>I<sub>RM</sub></b>				

**PLUS 247™ Outline**


Terminals: 1 - Gate  
 2 - Drain (Collector)  
 3 - Source (Emitter)  
 4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

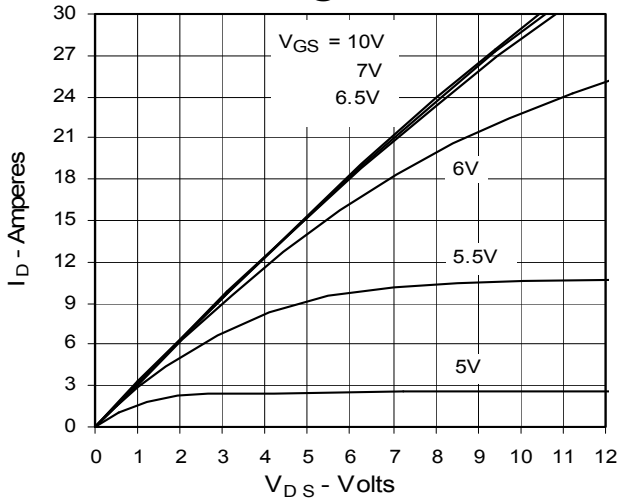
**TO-264 AA Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

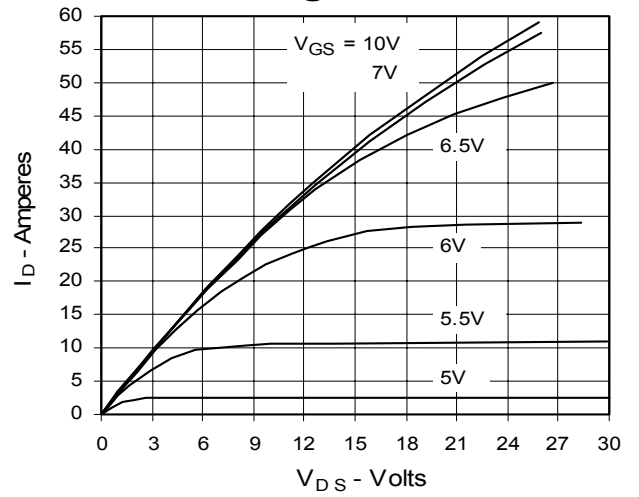
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343	6,583,505
	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344

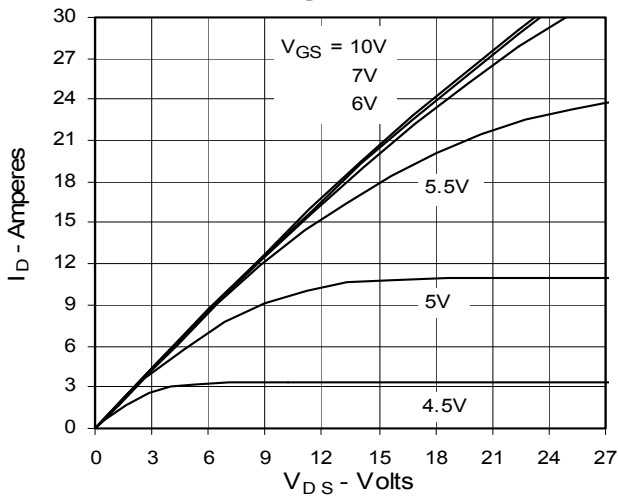
**Fig. 1. Output Characteristics**  
**@ 25°C**



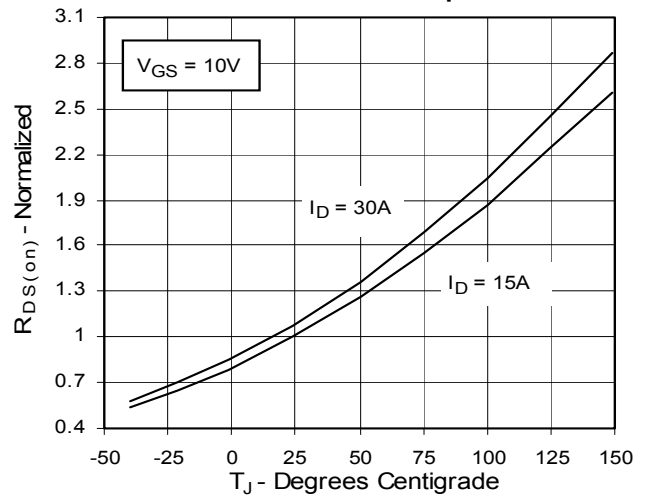
**Fig. 2. Extended Output Characteristics**  
**@ 25°C**



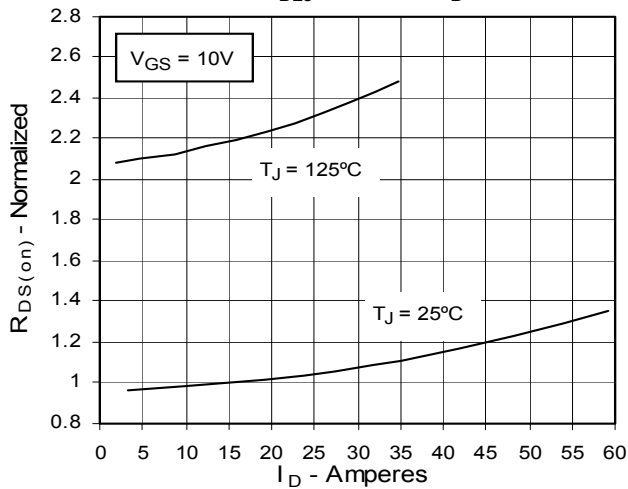
**Fig. 3. Output Characteristics**  
**@ 125°C**



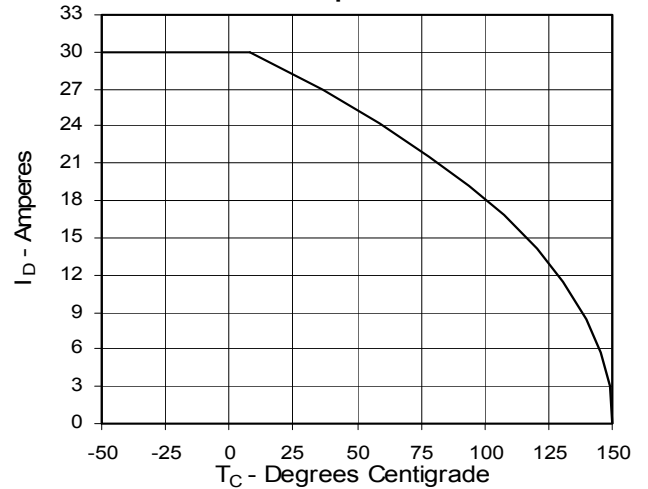
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**



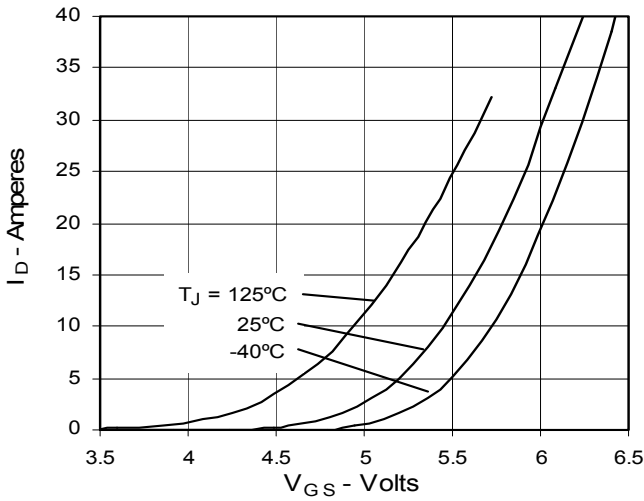
**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$**



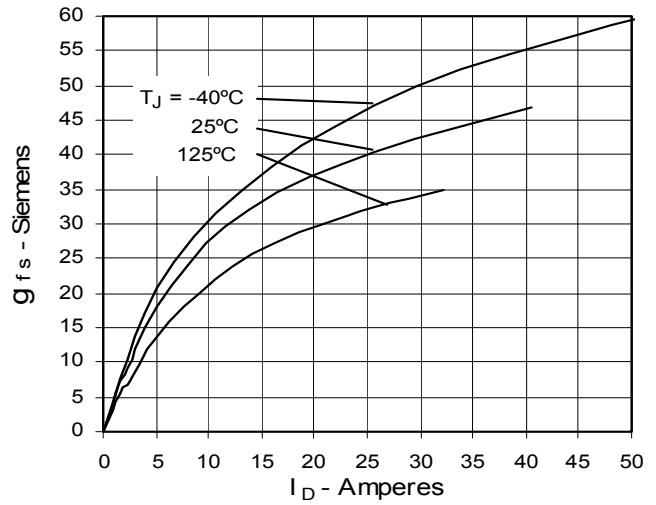
**Fig. 6. Drain Current vs. Case Temperature**



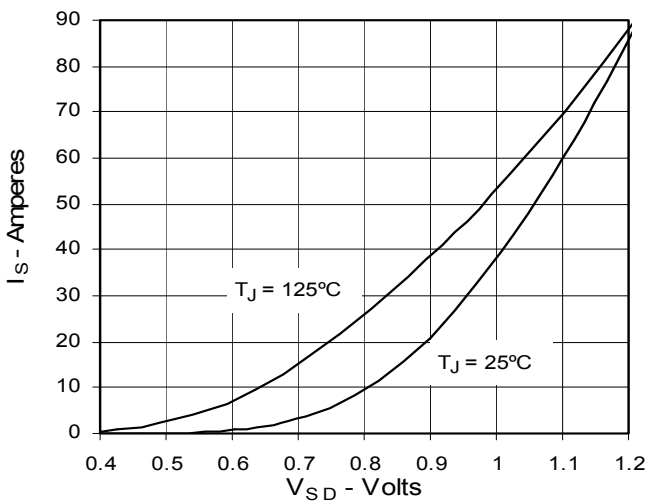
**Fig. 7. Input Admittance**



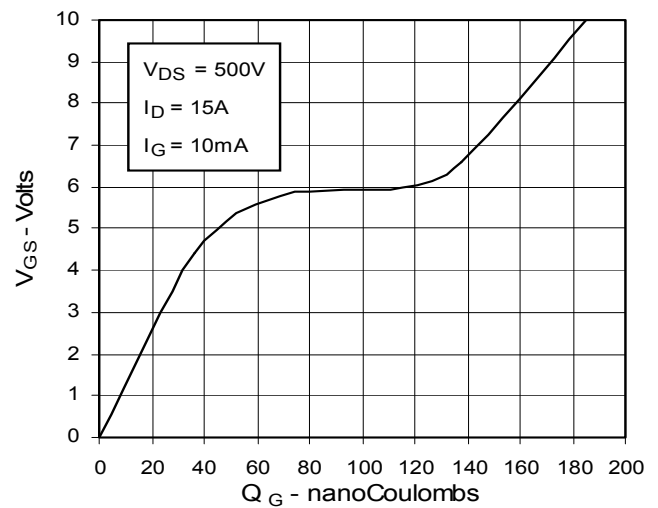
**Fig. 8. Transconductance**



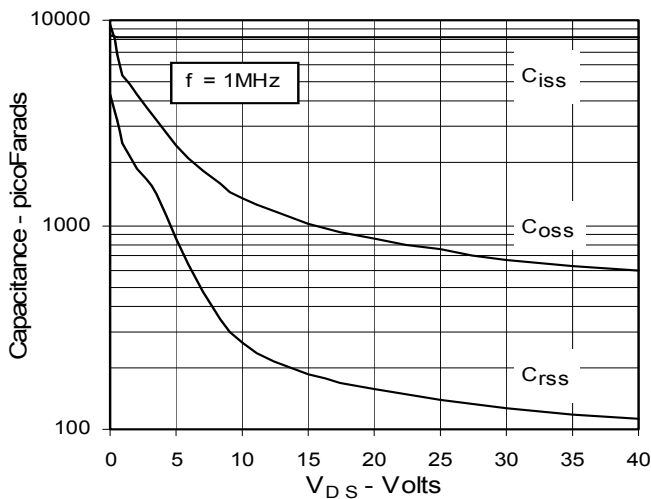
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



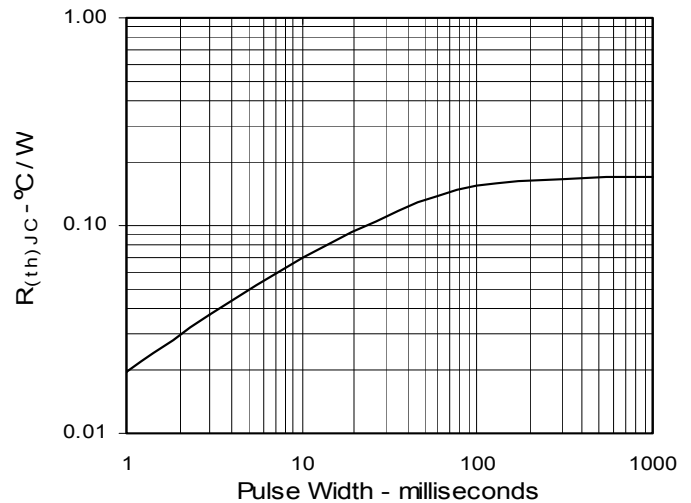
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**



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